

L Number	Hits	Search Text	DB	Time stamp
1	7877	(high with density) same (capacitor capacitive)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 21:40
2	2994	(ic (integrated adj circuit)) and ((high with density) same (capacitor capacitive))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 21:41
3	920	((ic (integrated adj circuit)) and ((high with density) same (capacitor capacitive))) and (stack stacking multilevel (multi adj level))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 21:43
4	859	((ic (integrated adj circuit)) and ((high with density) same (capacitor capacitive))) and (stack stacking multilevel (multi adj level)) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 21:43
5	728	((ic (integrated adj circuit)) and ((high with density) same (capacitor capacitive))) and (stack stacking multilevel (multi adj level)) and substrate and (interconnect connection connect interconnection)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 21:44

L Number	Hits	Search Text	DB	Time stamp
1	7877	(high with density) same (capacitor capacitive)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 21:46
2	2994	(ic (integrated adj circuit)) and ((high with density) same (capacitor capacitive))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 21:41
3	920	((ic (integrated adj circuit)) and ((high with density) same (capacitor capacitive))) and (stack stacking multilevel (multi adj level))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 21:43
4	859	((ic (integrated adj circuit)) and ((high with density) same (capacitor capacitive))) and (stack stacking multilevel (multi adj level)) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 21:43
5	728	((ic (integrated adj circuit)) and ((high with density) same (capacitor capacitive))) and (stack stacking multilevel (multi adj level)) and substrate and (interconnect connection connect interconnection)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 21:45
6	382	((ic (integrated adj circuit)) and ((high with density) same (capacitor capacitive))) and (stack stacking multilevel (multi adj level)) and substrate and (interconnect connection connect interconnection) and ((high with density) with (capacitor capacitive))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 21:47

L Number	Hits	Search Text	DB	Time stamp
1	7877	((high with density) same (capacitor capacitive))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/19 21:46
2	2994	((ic (integrated adj circuit)) and ((high with density) same (capacitor capacitive)))	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/19 21:41
3	920	((ic (integrated adj circuit)) and ((high with density) same (capacitor capacitive))) and (stack stacking multilevel (multi adj level))	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/19 21:43
4	859	(((ic (integrated adj circuit)) and ((high with density) same (capacitor capacitive))) and (stack stacking multilevel (multi adj level))) and substrate	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/19 21:43
5	728	(((ic (integrated adj circuit)) and ((high with density) same (capacitor capacitive))) and (stack stacking multilevel (multi adj level))) and substrate and (interconnect connection connect interconnection)	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/19 21:45
6	382	((((ic (integrated adj circuit)) and ((high with density) same (capacitor capacitive))) and (stack stacking multilevel (multi adj level))) and substrate and (interconnect connection connect interconnection)) and ((high with density) with (capacitor capacitive))	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/19 21:47